

GP 2822



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes
Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH
Docket No.: 303.229US2
Filed: August 11, 1998
Examiner: Mark V. Prenty
Serial No.: 09/132,157
Due Date: October 18, 2000
Group Art Unit: 2822

Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

A return postcard.
 An Amendment and Response (8 Pages).

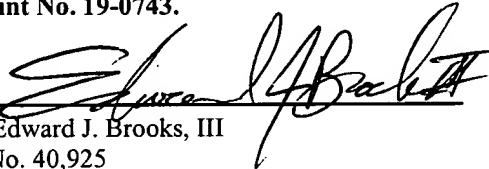
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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 18 day of October, 2000.

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S/N 09/132,157

PATENT

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Applicant: Leonard Forbes

Examiner: Mark V. Prenty

Serial No.: 09/132,157

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Title:

SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION
IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH



AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on July 18, 2000. Please amend the above-identified patent application as follows.

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IN THE CLAIMS

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Please amend the claims as follows:

11. (Four times amended) A p-channel metal-oxide-semiconductor transistor, comprising:
a silicon substrate;
a gate oxide, coupled to the substrate;
a gate, coupled to the gate oxide;
source/drain regions formed in the substrate on opposite sides of the gate; and
a $Si_{1-x}Ge_x$ channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining the gate oxide and between the source/drain regions;
wherein the $Si_{1-x}Ge_x$ channel region [is formed subsequent to formation of the gate oxide.] has a channel length less than 7 μm .

24. (Four times amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising:
a $Si_{1-x}Ge_x$ channel region, having a germanium molar fraction of x, and formed in the substrate, underneath and adjoining a gate oxide and between a source region and a drain region;